

FIG. 1

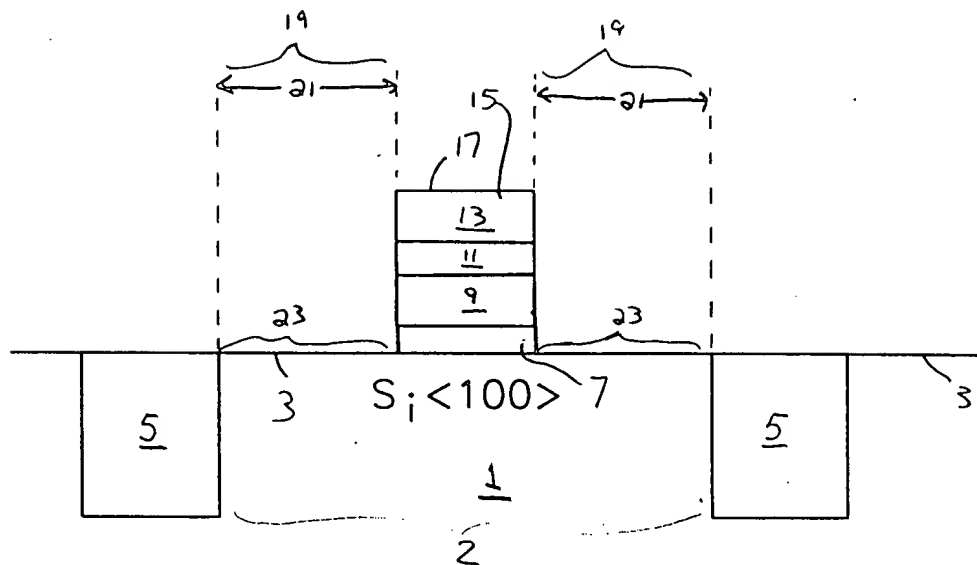


FIG. 2

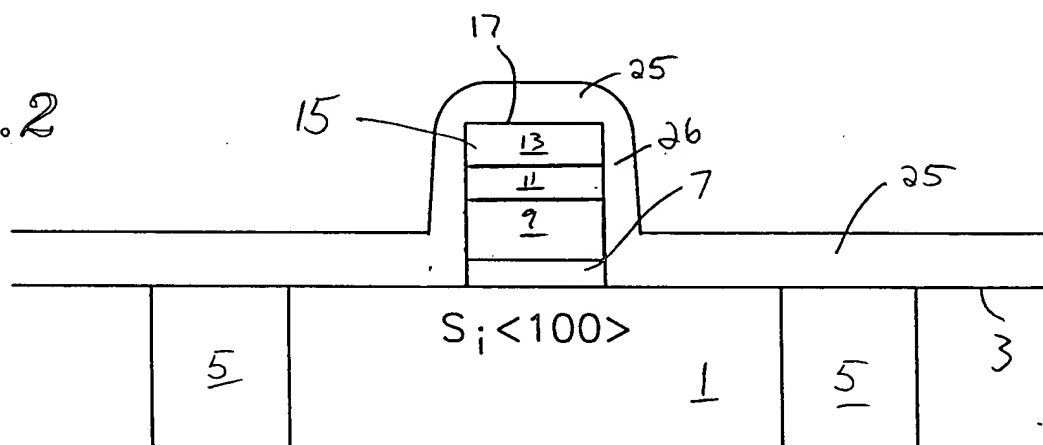


FIG. 3

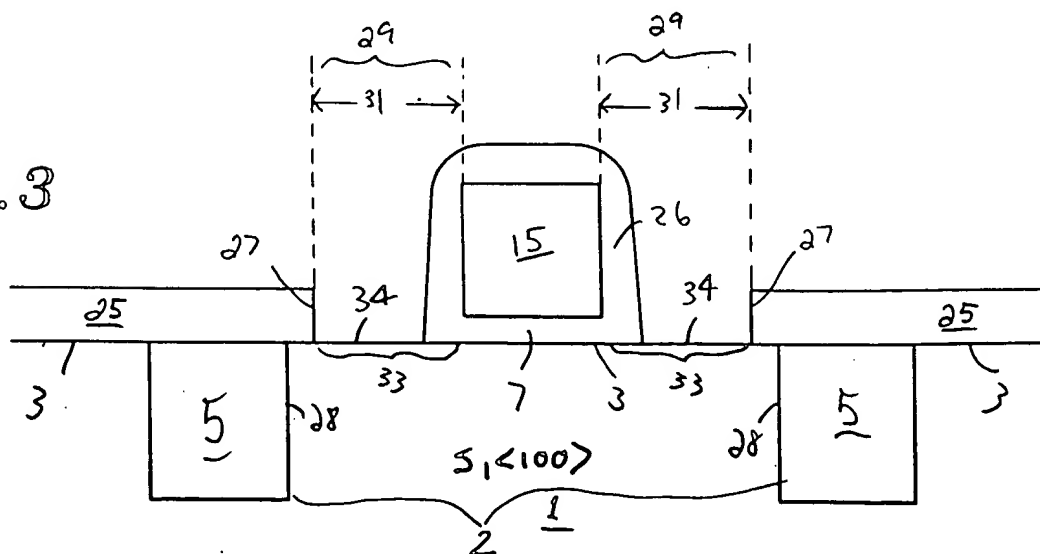


FIG. 4

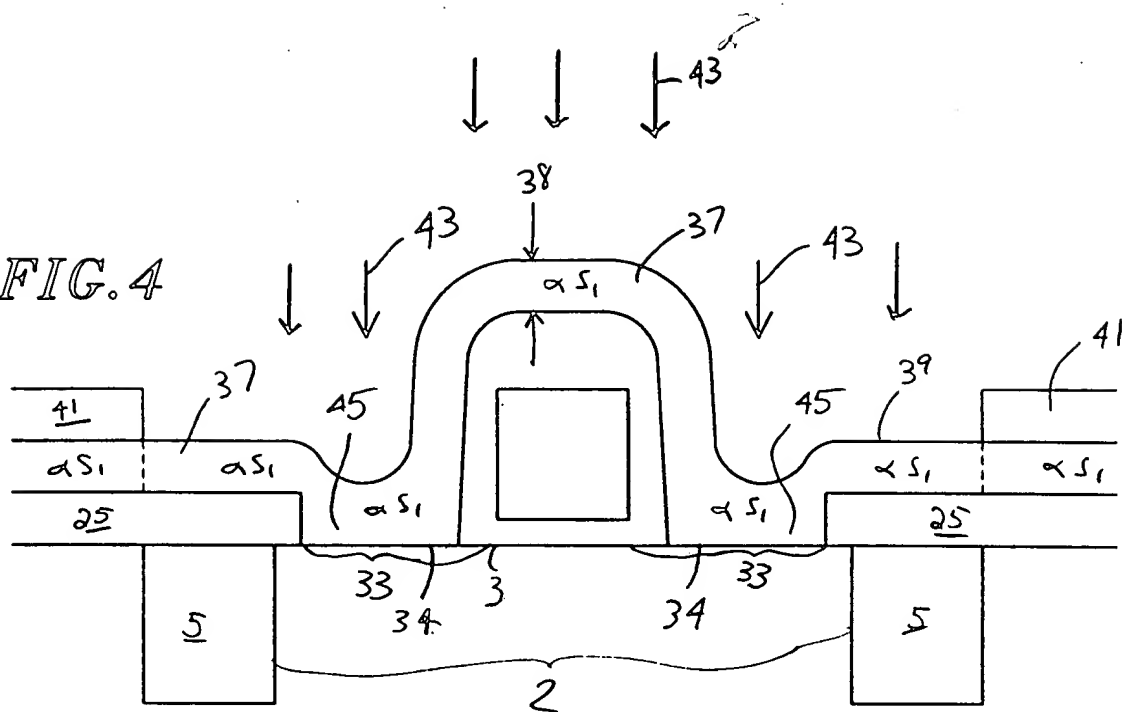


FIG. 5

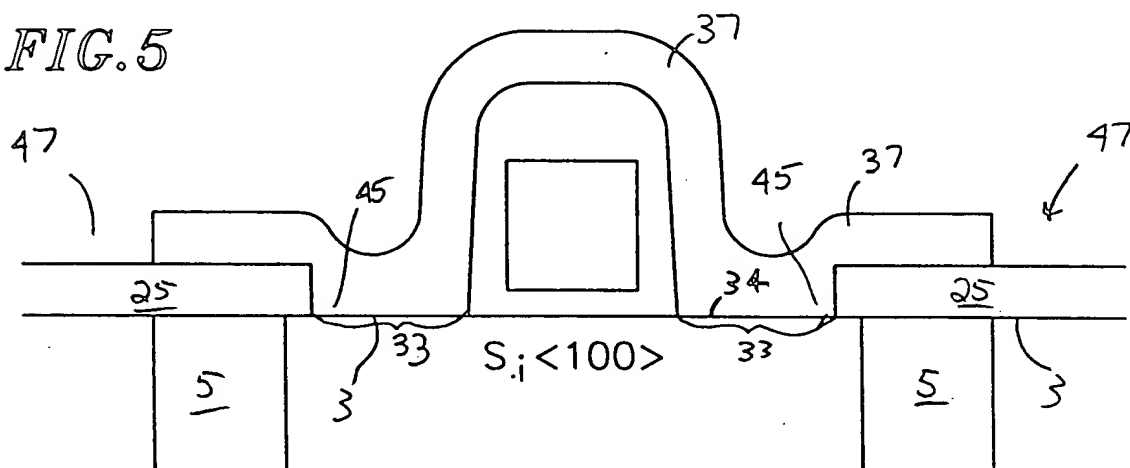


FIG. 7

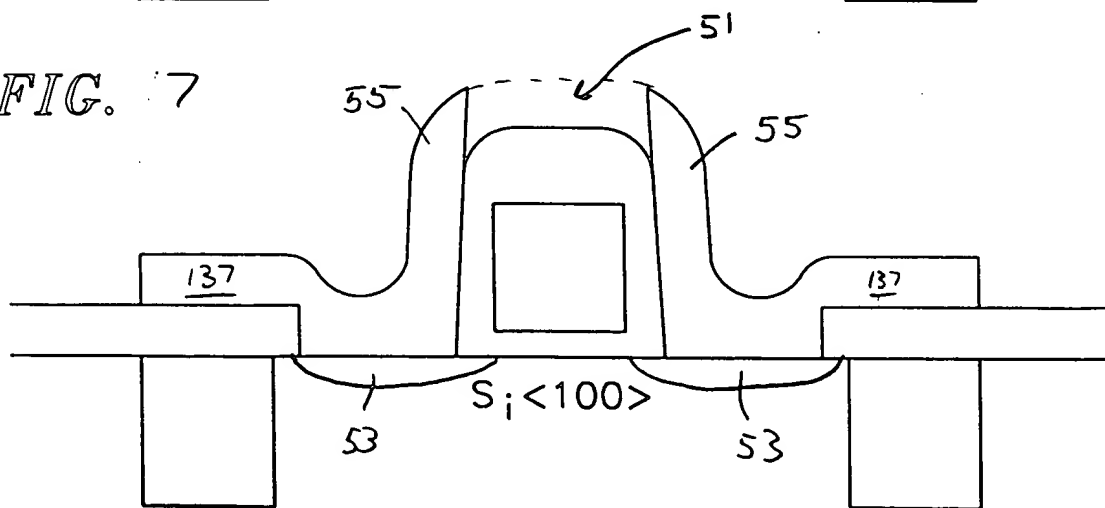


FIG. 8

A cross-sectional view of a semiconductor device. The device consists of a substrate (3) with several rectangular regions (5) embedded within it. On top of the substrate, there is a layer (3) which contains a series of rectangular structures (59). These structures are separated by recessed regions (67). Within each recessed region, there is a wavy line (63). A central square region (15) is located within one of the structures (59). The entire structure is labeled with various reference numerals: 5, 3, 59, 67, 63, 15, 17, 137, 53, 57, and Si<100>. Dimensions 69 and 71 are indicated.